ECH8697R

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N-Channel Power MOSFET 24V, 10A, 11.6mΩ, Dual ECH8 Common Drain

Features

- Low On-resistance
- 2.5V drive
- Common-Drain Type
- Protection diode in

- Built-in gate protection resistor
- Best suited for LiB charging and discharging switch
- Halogen free compliance

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain to Source Voltage	VDSS		24	V
Gate to Source Voltage	VGSS		±12.5	V
Drain Current (DC)	ID		10	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	60	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate(1000mm ² ×0.8mm) 1unit	1.5	W
Total Dissipation	PT	When mounted on ceramic substrate(1000mm ² ×0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		- 55 to +150	°C

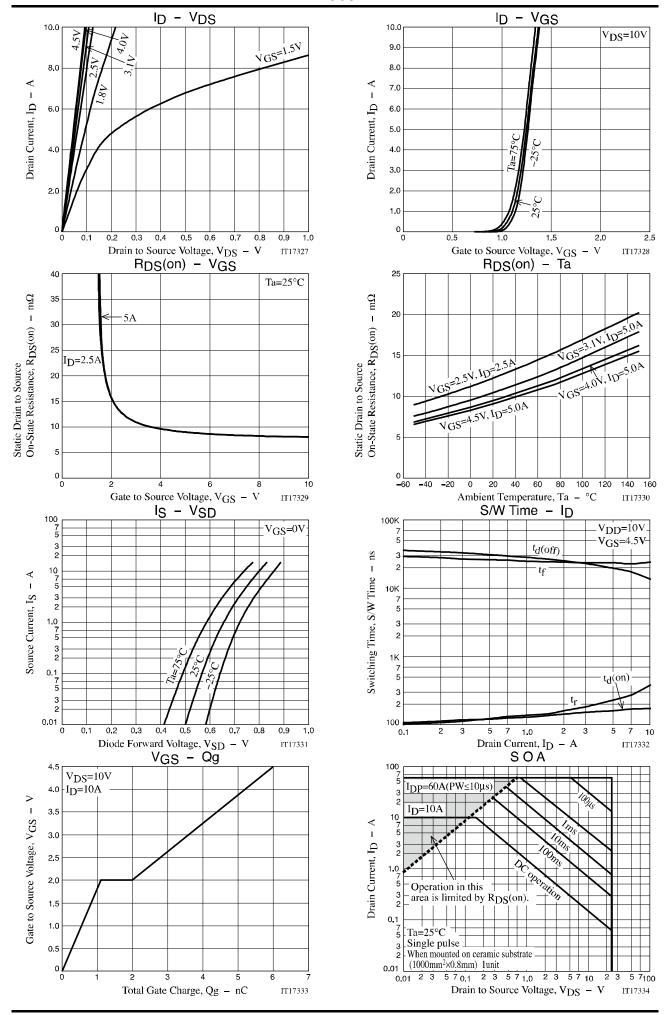
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

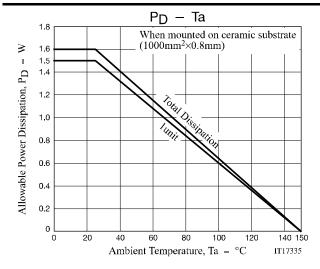
Electrical Characteristics at Ta = 25°C

	Symbol		Ratings			
Parameter		Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	24			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±1	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	0.5		1.3	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =5A		5.0		S
	R _{DS} (on)1	I _D =5A, V _{GS} =4.5V	7.4	9.3	11.6	mΩ
	R _{DS} (on)2	I _D =5A, V _{GS} =4.0V	7.7	9.7	12.6	mΩ
Static Drain to Source On-State Resistance	R _{DS} (on)3	I _D =5A, V _{GS} =3.1V	8.5	10.7	15	mΩ
	R _{DS} (on)4	I _D =2.5A, V _{GS} =2.5V	10	12.5	17.5	mΩ
Turn-ON Delay Time	t _d (on)			160		ns
Rise Time	t _r	0		230		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		19700		ns
Fall Time	tf			23600		ns
Total Gate Charge	Qg			6		nC
Gate to Source Charge	Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =10A		1.1		nC
Gate to Drain "Miller" Charge	Qgd			0.9		nC
Diode Forward Voltage	V _{SD}	I _S =10A, V _{GS} =0V		0.8	1.2	V

ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.





Package Dimensions

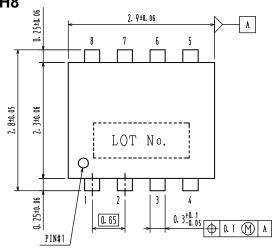
ECH8697R-TL-W

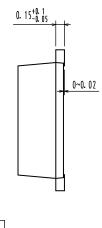
SOT-28FL/ECH8

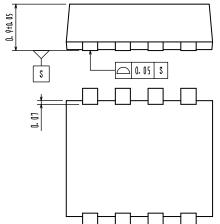
CASE 318BF ISSUE O

Unit: mm

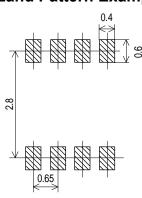
- 1: Source1
- 2: Gate1
- 3: Source2
- 4: Gate2
- 5: Drain
- 6: Drain
- 7: Drain
- 8: Drain







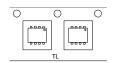
Land Pattern Example



Ordering & Package Information

•	•		
Device	Package	Shipping	note
ECH8697R-TL-W	ECH8	3,000 pcs. / reel	Pb-Free and Halogen Free

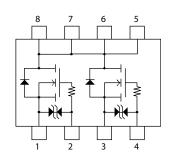
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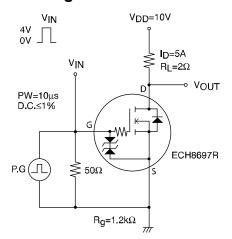
Marking



Electrical Connection



Switching Time Test Circuit



ECH8697R

Note on usage: Since the ECH8697R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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